

DESCRIPTION

Microsemi's 100 kW Transient Voltage Suppressors (TVSs) are designed for aircraft applications requiring high power transient protection with a comparatively small axial-leaded package size. This includes various threats such as "Waveform 4" at 6.4/69 μ s per **RTCA/DO-160E** Section 22. It is also available with screening in accordance with MIL-PRF-19500 or avionics screening as described in the Features section herein. It may also be optionally acquired with RoHS Compliant (annealed matte-Tin finish) with an e3 suffix added to the part number. Microsemi also offers a broad spectrum of other TVSs to meet your needs.

IMPORTANT: For the most current data, consult *MICROSEMI's* website: <http://www.microsemi.com>

APPEARANCE



FEATURES

- Available in both Unidirectional and Bidirectional construction (Bidirectional with CA suffix)
- TVS selection for 33 to 400 V Standoff Voltages (V_{WM})
- Suppresses transients up to **100 kW @ 6.4/69 μ s**
- Fast response with less than 5 ns turn-on time.
- Optional 100% **screening for avionics grade** is available by adding **MA** prefix to part number for added 100% temperature cycle -55°C to +125°C (10X), surge (3X) in each direction, 24 hours HTRB in each direction, and post test (V_{BR} and I_D)
- Options for **screening** in accordance with MIL-PRF-19500 for **JAN, JANTX, and JANTXV** are also available by adding MQ, MX, or MV prefixes respectively to part numbers.
- Moisture classification is Level 1 with no dry pack required per IPC/JEDEC J-STD-020B.
- RoHS Compliant devices available by adding "e3" suffix

APPLICATIONS / BENEFITS

- Protection from high power switching transients, induced RF, and lightning threats with comparatively small package size (0.25 inch diameter)
- Protection from ESD and EFT per IEC61000-4-2 and IEC61000-4-4
- Pin injection protection per RTCA/DO-160E up to Level 4 for Waveform 4 (6.4/69 μ s) on all devices
- Pin injection protection per RTCA/DO-160E up to Level 5 for Waveform 4 (6.4/69 μ s) on device types RT100KP33A or CA up to RT100KP260A or CA
- Pin injection protection per RTCA/DO-160E up to Level 3 for Waveform 5A (40/120 μ s) on all devices
- Pin injection protection per RTCA/DO-160E up to Level 4 for Waveform 5A (40/120 μ s) on device types RT100KP33A or CA up to RT100KP64A or CA
- Consult Factory for other voltages with similar Peak Pulse Power capabilities.

MAXIMUM RATINGS

- Peak Pulse Power dissipation at 25°C: 100 kW at 6.4/69 μ s waveform in Figure 8 (also see figures 1 and 2)
- Impulse repetition rate: 0.005%
- $t_{clamping}$ (0 volts to V_{BR} min): <100 ps theoretical for unidirectional and <5 ns for bidirectional
- Operating & storage temperatures: -65°C to +150°C
- Thermal resistance: 17.5C/W junction to lead, or 77.5C/W junction to ambient when mounted on FR4 PC board with 4 mm² copper pads (1 oz) and track width 1 mm, length 25 mm
- Steady-state power dissipation: 7 Watts @ $T_L = 27.5^\circ\text{C}$ or 1.61 Watts at $T_A = 25^\circ\text{C}$ when mounted on FR4 PC Board described for thermal resistance above
- Forward surge: 250 Amps 8.3 ms half-sine wave for unidirectional devices only
- Solder Temperatures: 260°C for 10 s maximum

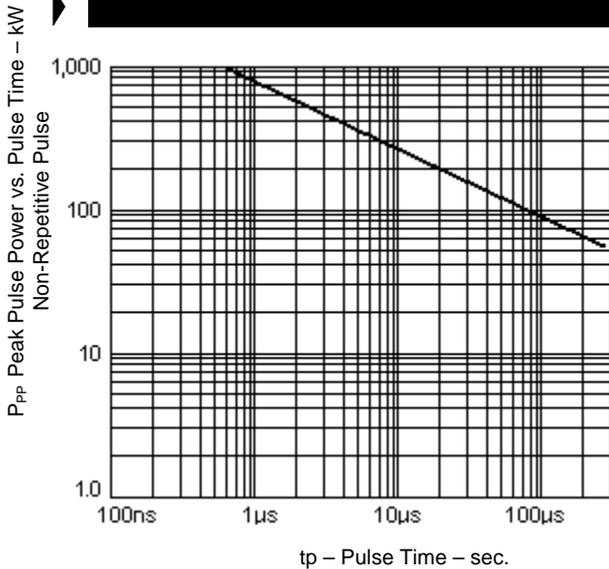
MECHANICAL & PACKAGING

- CASE: Void free transfer molded thermosetting epoxy meeting UL94V-O requirements
- FINISH: Tin-Lead or RoHS Compliant matte-Tin plating solderable per MIL-STD-750, method 2026
- Polarity: Cathode marked with band for unidirectional (no band required for bi-directional)
- MARKING: Manufacturers logo and part number. Add prefix MA, MQ, MX, etc., for screened parts.
- WEIGHT: 1.7 grams (approximate)
- TAPE & REEL option: Standard per EIA-296 for axial package (add "TR" suffix to part number)
- Package dimensions: See last page

ELECTRICAL CHARACTERISTICS at 25°C

Part Number (1) (4)	Rated Stand-off Voltage V_{WM}	Breakdown Voltage $V_{(BR)}$ Volts @ $I_{(BR)}$		Maximum Clamping @ I_{PP} (2) V_C	Maximum Reverse Leakage @ V_{WM} I_D	Maximum Peak Pulse Current (3) @ 6.4/69 μs I_{PP}	Maximum $V_{(BR)}$ temperature Coefficient $\alpha_{V(BR)}$
		VOLTS	mA				
<i>RT100KP33A</i>	33	36.7-40.6	50	58.6	5000	1825 *	38
<i>RT100KP36A</i>	36	40.0-44.2	50	61.8	5000	1672 *	41
RT100KP40A	40	44.4-49.1	20	68.6	1500	1518 *	46
<i>RT100KP43A</i>	43	47.8-52.8	10	71.0	500	1432 *	50
<i>RT100KP45A</i>	45	50.0-55.3	5	73.0	150	1365 *	52
<i>RT100KP48A</i>	48	53.3-58.9	5	77.7	150	1285 *	56
RT100KP51A	51	56.7-62.7	5	82.8	50	1205 *	60
RT100KP54A	54	60.0-66.3	5	87.5	25	1139 *	63
RT100KP58A	58	64.4-71.2	5	94.0	15	1066 *	68
RT100KP60A	60	66.7-73.7	5	97.3	15	1012 *	71
RT100KP64A	64	71.1-78.6	5	104	10	959 *	76
<i>RT100KP70A</i>	70	77.8-86.0	5	114	10	879	83
<i>RT100KP75A</i>	75	83.3-92.1	5	122	10	819	89
<i>RT100KP78A</i>	78	86.7-95.8	5	126	10	793	93
RT100KP85A	85	94.4-104	5	137	10	726	102
RT100KP90A	90	100-111	5	146	10	686	109
RT100KP100A	100	111-123	5	162	10	619	121
RT100KP110A	110	122-135	5	178	10	559	133
RT100KP120A	120	133-147	5	193	10	519	145
RT100KP130A	130	144-159	5	209	10	473	157
RT100KP150A	150	167-185	5	243	10	413	183
RT100KP160A	160	178-197	5	259	10	386	195
<i>RT100KP170A</i>	170	189-209	5	275	10	366	207
<i>RT100KP180A</i>	180	200-221	5	291	10	346	219
<i>RT100KP200A</i>	200	222-245	5	322	10	313	243
<i>RT100KP220A</i>	220	245-271	5	356	10	280	269
RT100KP250A	250	278-308	5	403	10	246	306
RT100KP260A	260	289-320	5	419	10	236	318
<i>RT100KP280A</i>	280	311-345	5	451	10	220	344
<i>RT100KP300A</i>	300	333-369	5	483	10	206	368
<i>RT100KP350A</i>	350	389-431	5	564	10	176	430
<i>RT100KP400A</i>	400	444-492	5	644	10	153	490

- For bidirectional construction, indicate a CA suffix (instead of A) after the part number
- Clamping voltage does not include any variable parasitic lead inductance effects observed during the 6.4 μs rise time due to lead length.
- The Maximum Peak Pulse Current (I_{PP}) shown represents the performance capabilities by design.
* Surge test screening is only performed up to 900 Amps (test equipment limitations).
- Part numbers in bold italics are preferred devices.



tp - Pulse Time - sec.

FIGURE 1

Peak Pulse Power vs. Pulse Time
To 50% of Exponentially Decaying Pulse

NOTE: This P_{PP} versus time graph allows the designer to use these parts over a broad power spectrum using the guidelines illustrated in App Note 104 on Microsemi's website. Aircraft transients are described with exponential decaying waveforms. For suppression of square-wave impulses, derate power and current to 66% of that for exponential decay shown in Figure 1.

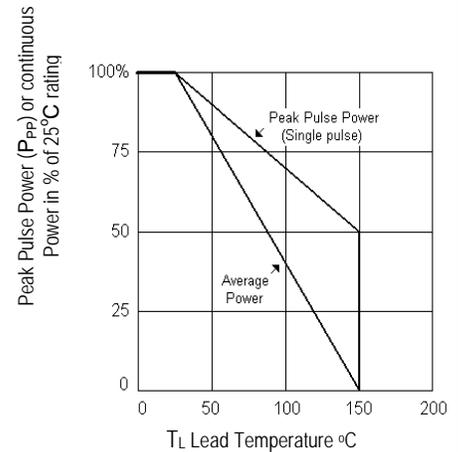


FIGURE 2

POWER DERATING

INSTALLATION

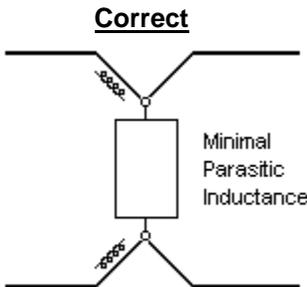


FIGURE 3

TVS devices used across power lines are subject to relatively high magnitude surge currents and are more prone to adverse parasitic inductance effects in the mounting leads. Minimizing the shunt path of the lead inductance and their $V = -L di/dt$ effects will optimize the TVS effectiveness. Examples of optimum installation and poor installation are illustrated in figures 3 through figure 6. Figure 3 illustrates minimal parasitic inductance with attachment at end of device. Inductive voltage drop is across input leads. Virtually no "overshoot" voltage results as illustrated with figure 4. The loss of effectiveness in protection caused by excessive parasitic inductance is illustrated in figures 5 and 6. Also see MicroNote 111 for further information on "Parasitic Lead Inductance in TVS".

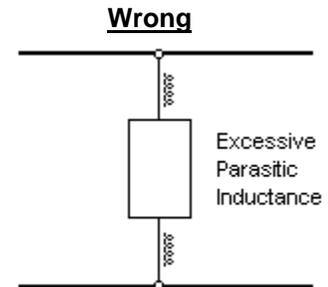


FIGURE 5

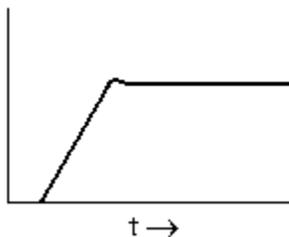


FIGURE 4

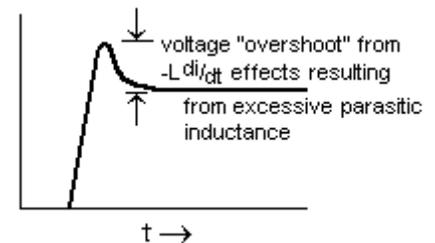
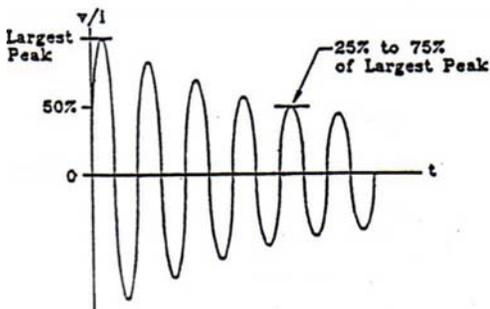


FIGURE 6



t – time
Note: frequency is 1MHz
FIGURE 7 – Waveform 3

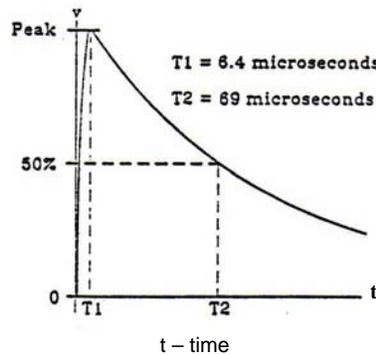


FIGURE 8 – Waveform 4

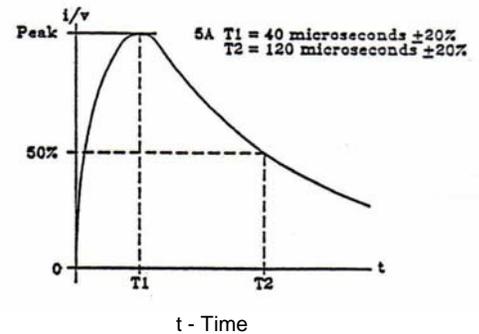


FIGURE 9 – Waveform 5A

NOTE: The 1MHz damped oscillatory waveform (3) has an effective pulse width of 4 μ s. Equivalent peak pulse power at each of the pulse widths represented in RTCA/DO-160E for waveforms 3, 4 and 5A (above) have been determined referencing Figure 1 herein as well as Application Notes 104 and 120 (found on Microsemi's website) and are listed below.

WAVEFORM NUMBER	PULSE WIDTH μ s	PEAK PULSE POWER kW	Peak Pulse Current Conversion Factor * from Rated I_{PP} at 6.4/69 μ s
3	4	340	3.40x
4	6.4/69	100	1.00x
5A	40/120	70	0.70x

* Multiply by the conversion factor shown with reference to the maximum rated I_{PP} in the Electrical Characteristics Table on page 2.

Note: High current fast rise-time transients of 250 ns or less can more than triple the V_C from parasitic inductance effects ($V = -Ldi/dt$) compared to the clamping voltage shown in the initial Electrical Characteristics on page 1 as also described in Figures 5 and 6 herein.

Also see MicroNotes 127, 130, and 132 on the Microsemi website (Support section) for further information on Transient Voltage Suppressors with reference to aircraft industry specification RTCA/DO-160E.

DIMENSIONS

